

Product Summary

| $V_{(BR)DSS}$ | $R_{DS(on)}$ | I_D $T_A = 25^\circ C$ |
|---------------|----------------------------------|-----------------------------|
| -60V | 125m Ω @ $V_{GS} = -10V$ | -6.6A |
| | 190m Ω @ $V_{GS} = -4.5V$ | -5.3A |

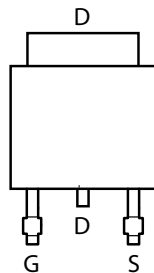
Description and Applications

This new generation MOSFET has been designed to minimize the on-state resistance ($R_{DS(on)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

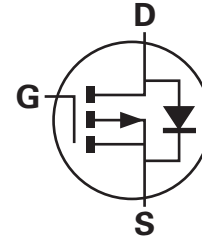
- Backlighting
- DC-DC Converters
- Power management functions



Top View



Pin Out -Top View



Equivalent Circuit

Features and Benefits

- Low on-resistance
- Fast switching speed
- "Green" component and RoHS compliant (Note 1)

Mechanical Data

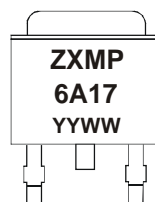
- Case: TO252-3L
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0 (Note 1)
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals Connections: See Diagram
- Terminals: Matte Tin Finish annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.33 grams (approximate)

Ordering Information (Note 1)

| Product | Marking | Reel size (inches) | Tape width (mm) | Quantity per reel |
|-------------|-----------|--------------------|-----------------|-------------------|
| ZXMP6A17KTC | See Below | 13 | 16 | 2,500 |

Note: 1. Diodes, Inc. defines "Green" products as those which are Eu RoHS compliant and contain no halogens or antimony compounds; further information about Diodes Inc.'s "Green" Policy can be found on our website. For packaging details, go to our website.

Marking Information



ZXMP = Product Type Marking Code, Line 1
 6A17 = Product Type Marking Code, Line 2
 YYWW = Date Code Marking
 YY = Year (ex: 09 = 2009)
 WW = Week (01-52)

Maximum Ratings @ $T_A = 25^\circ\text{C}$ unless otherwise specified

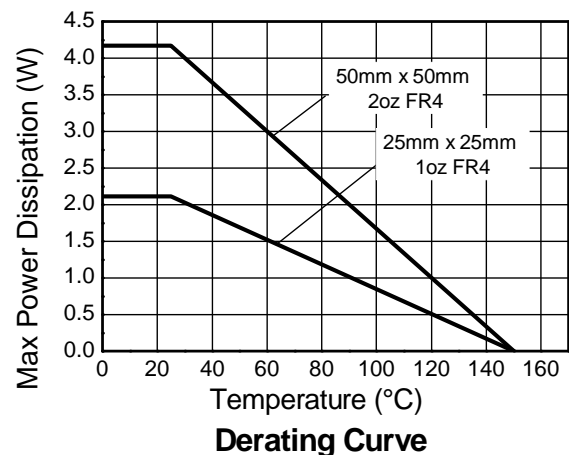
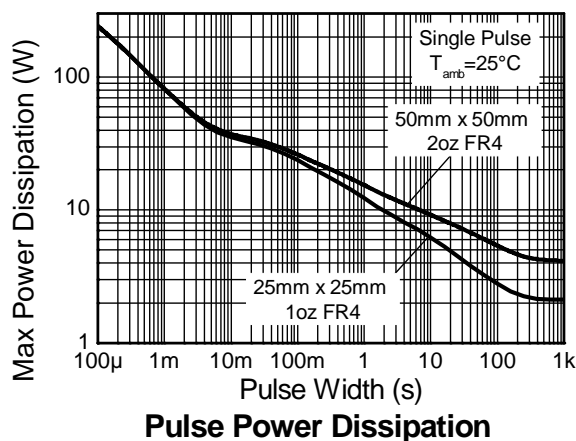
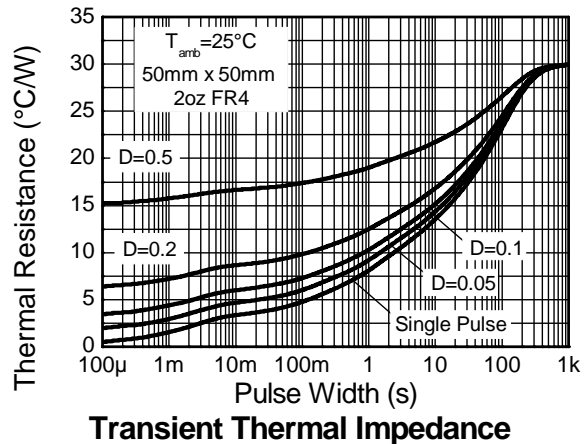
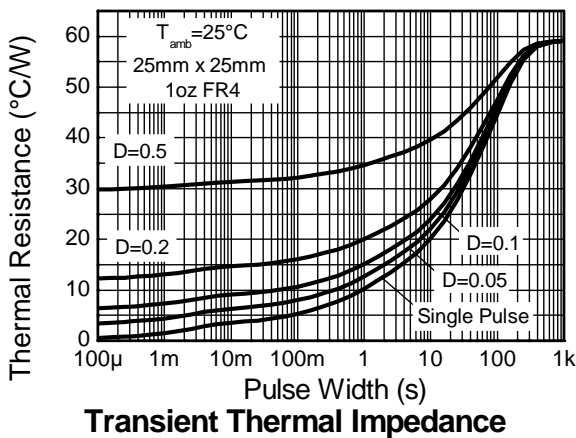
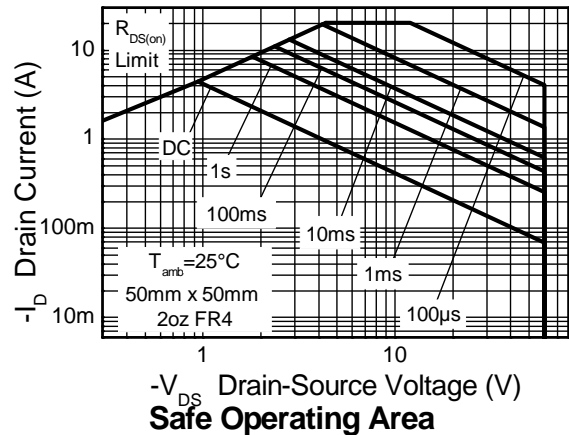
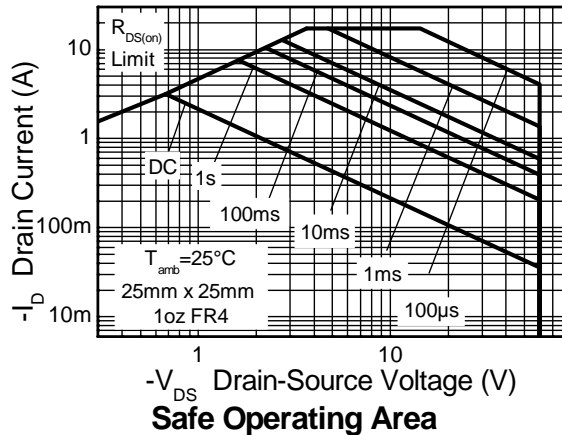
| Characteristic | | | Symbol | Value | Unit | |
|--|-----------------------|-----------------------------------|----------|----------|------|---|
| Drain-Source voltage | | | V_{DS} | -60 | V | |
| Gate-Source voltage | | | V_{GS} | ± 20 | V | |
| Continuous Drain current | $V_{GS} = 10\text{V}$ | (Note 3) | I_D | 6.6 | A | |
| | | $T_A = 70^\circ\text{C}$ (Note 3) | | 5.3 | | |
| | | (Note 2) | | 4.4 | | |
| Pulsed Drain current | $V_{GS} = 10\text{V}$ | (Note 4) | I_{DM} | 20.3 | A | |
| Continuous Source current (Body diode) | | | (Note 3) | I_S | 9.3 | A |
| Pulsed Source current (Body diode) | | | (Note 4) | I_{SM} | 20.3 | A |

Thermal Characteristics @ $T_A = 25^\circ\text{C}$ unless otherwise specified

| Characteristic | | Symbol | Value | Unit |
|---|----------|-----------------|------------|---------------------------|
| Power dissipation Linear derating factor | (Note 2) | P_D | 4.17 | W mW/ $^\circ\text{C}$ |
| | | | 33.3 | |
| | (Note 3) | | 9.25 | |
| | (Note 5) | | 74.0 | |
| Thermal Resistance, Junction to Ambient | (Note 2) | $R_{\theta JA}$ | 2.11 | $^\circ\text{C/W}$ |
| | (Note 3) | | 16.8 | |
| | (Note 5) | | 30.0 | |
| Thermal Resistance, Junction to Lead | (Note 3) | $R_{\theta JL}$ | 13.5 | $^\circ\text{C/W}$ |
| | (Note 5) | | 59.1 | |
| Operating and storage temperature range | | T_J, T_{STG} | -55 to 150 | $^\circ\text{C}$ |

- Notes:
2. For a device surface mounted on 50mm x 50mm x 1.6mm FR4 PCB with high coverage of single sided 2oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
 3. Same as note 2, except the device is measured at $t \leq 10$ sec.
 4. Same as note 2, except the device is pulsed with $D = 0.02$ and pulse width 300 μs . The pulse current is limited by the maximum junction temperature.
 5. For a device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
 6. Thermal resistance from junction to solder-point (at the end of the drain lead).

Thermal Characteristics

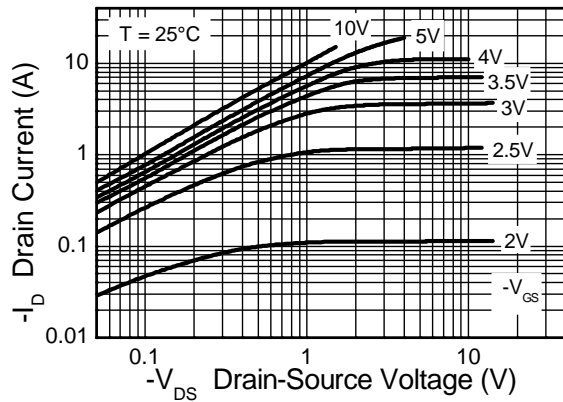


Electrical Characteristics @T_A = 25°C unless otherwise specified

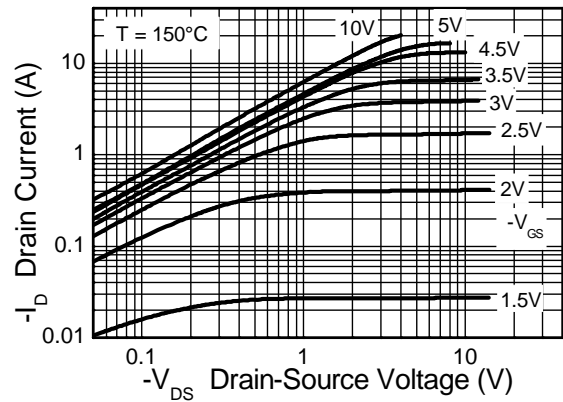
| Characteristic | Symbol | Min | Typ | Max | Unit | Test Condition |
|--|---------------------|------|-------|-------|------|---|
| OFF CHARACTERISTICS | | | | | | |
| Drain-Source Breakdown Voltage | BV _{DSS} | -60 | — | — | V | I _D = -250μA, V _{GS} = 0V |
| Zero Gate Voltage Drain Current | I _{DSS} | — | — | -0.5 | μA | V _{DS} = -60V, V _{GS} = 0V |
| Gate-Source Leakage | I _{GSS} | — | — | ±100 | nA | V _{GS} = ±20V, V _{DS} = 0V |
| ON CHARACTERISTICS | | | | | | |
| Gate Threshold Voltage | V _{GS(th)} | -1.0 | — | — | V | I _D = -250μA, V _{DS} = V _{GS} |
| Static Drain-Source On-Resistance (Note 7) | R _{DS(on)} | — | — | 0.125 | Ω | V _{GS} = -10V, I _D = -2.3A |
| | | | | 0.190 | | V _{GS} = -4.5V, I _D = -1.9A |
| Forward Transconductance (Notes 7 & 8) | g _{fs} | — | 4.7 | — | S | V _{DS} = -15V, I _D = -2.2A |
| Diode Forward Voltage (Note 7) | V _{SD} | — | -0.85 | -0.95 | V | I _S = -2A, V _{GS} = 0V |
| Reverse recovery time (Note 8) | t _{rr} | — | 25.1 | — | ns | I _S = -1.7A, di/dt = 100A/μs |
| Reverse recovery charge (Note 8) | Q _{rr} | — | 27.2 | — | nC | |
| DYNAMIC CHARACTERISTICS (Note 8) | | | | | | |
| Input Capacitance | C _{iss} | — | 637 | — | pF | V _{DS} = -30V, V _{GS} = 0V f = 1MHz |
| Output Capacitance | C _{oss} | — | 70 | — | pF | |
| Reverse Transfer Capacitance | C _{rss} | — | 53 | — | pF | |
| Total Gate Charge | Q _g | — | 9.0 | — | nC | V _{GS} = -4.5V |
| Total Gate Charge | Q _g | — | 17.7 | — | nC | V _{GS} = -10V |
| Gate-Source Charge | Q _{gs} | — | 1.6 | — | nC | |
| Gate-Drain Charge | Q _{gd} | — | 4.4 | — | nC | |
| Turn-On Delay Time (Note 9) | t _{D(on)} | — | 2.6 | — | ns | V _{DD} = -30V, V _{GS} = -10V I _D = -1A, R _G ≅ 6.0Ω |
| Turn-On Rise Time (Note 9) | t _r | — | 3.4 | — | ns | |
| Turn-Off Delay Time (Note 9) | t _{D(off)} | — | 26.2 | — | ns | |
| Turn-Off Fall Time (Note 9) | t _f | — | 11.3 | — | ns | |

- Notes:
7. Measured under pulsed conditions. Pulse width ≤ 300μs; duty cycle ≤ 2%
 8. For design aid only, not subject to production testing.
 9. Switching characteristics are independent of operating junction temperatures.

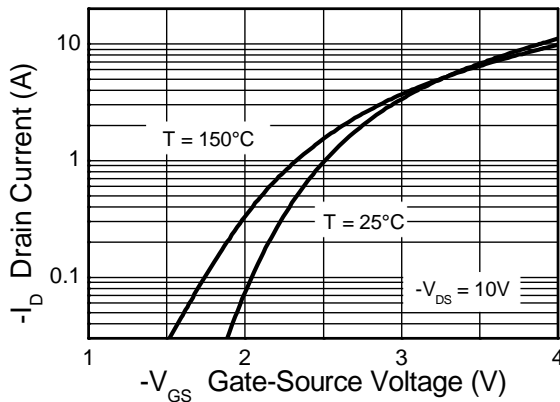
Typical Characteristics



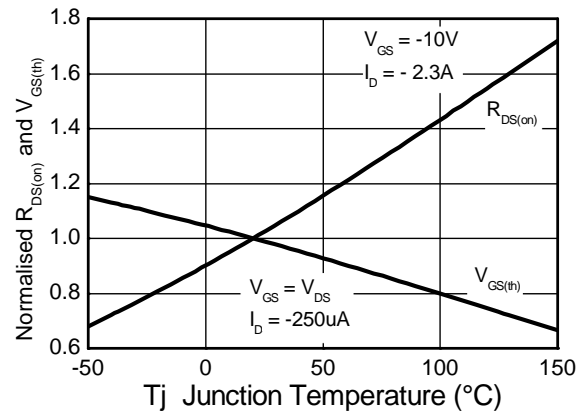
Output Characteristics



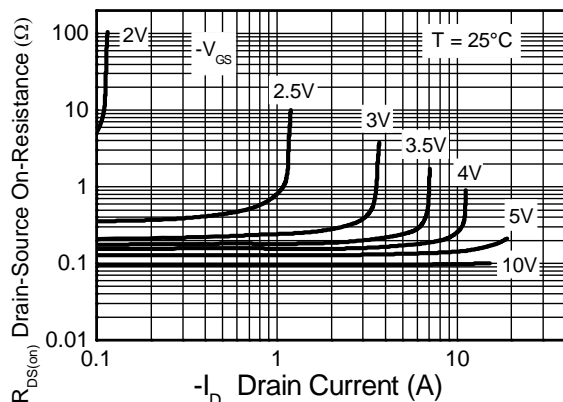
Output Characteristics



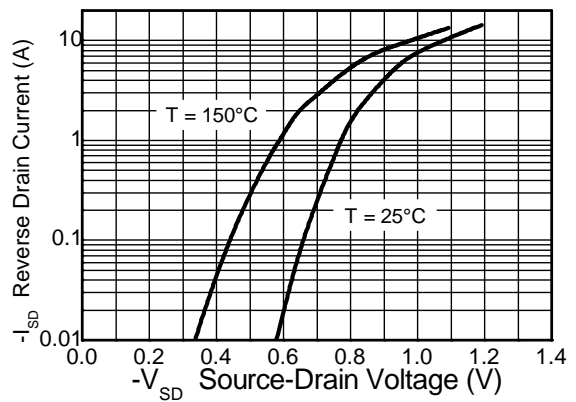
Typical Transfer Characteristics



Normalised Curves v Temperature

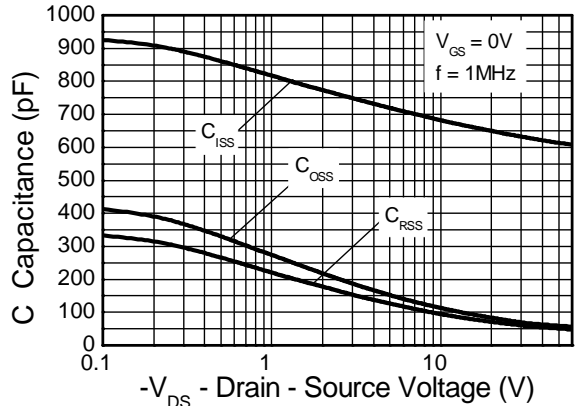


On-Resistance v Drain Current

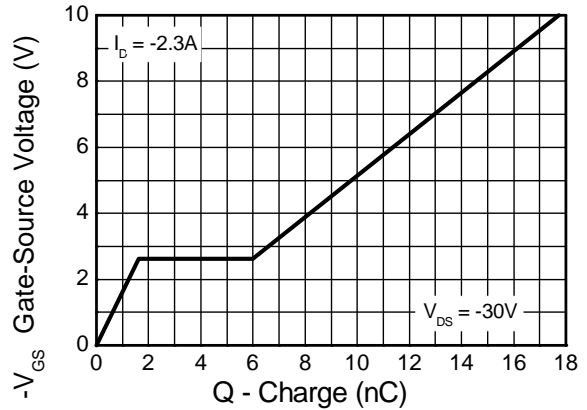


Source-Drain Diode Forward Voltage

Typical Characteristics - continued

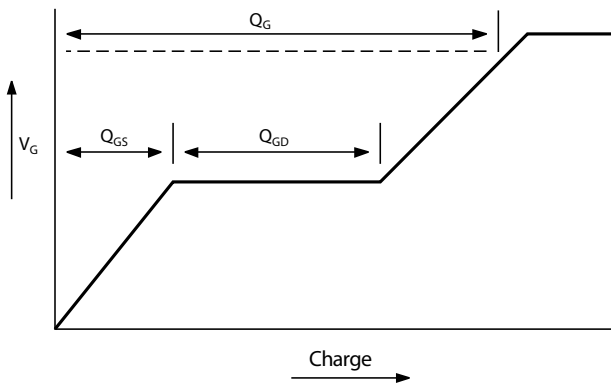


Capacitance v Drain-Source Voltage

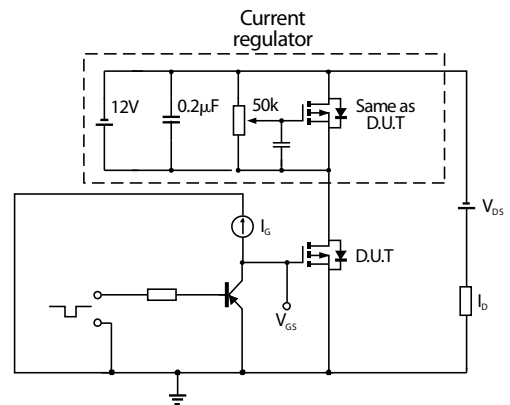


Gate-Source Voltage v Gate Charge

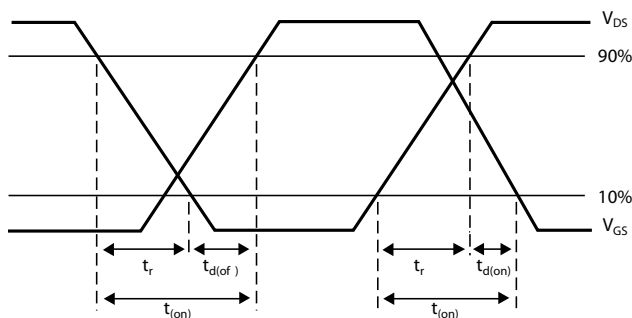
Test Circuits



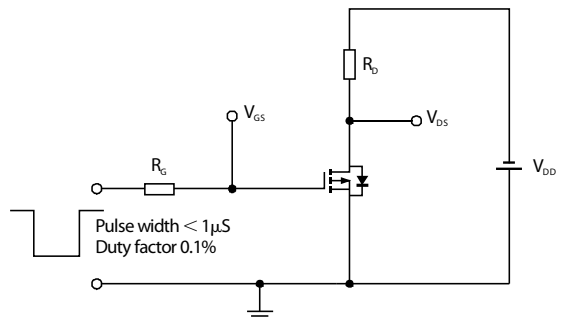
Basic gate charge waveform



Gate charge test circuit

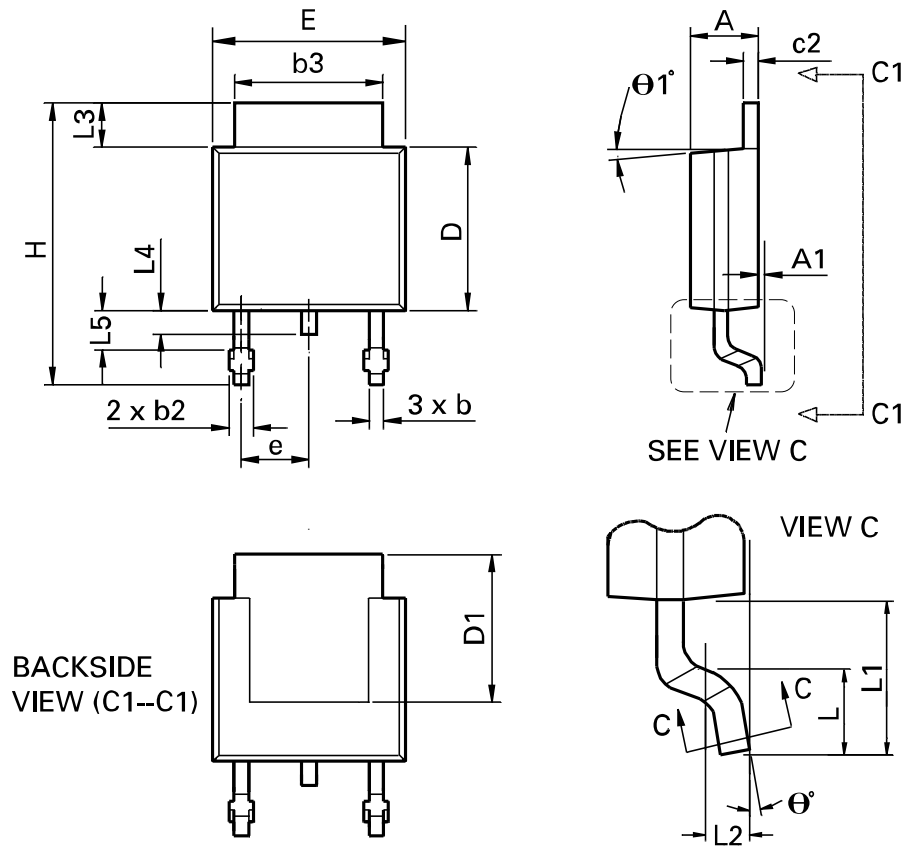


Switching time waveforms



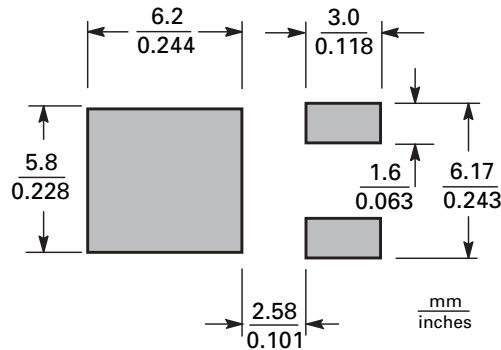
Switching time test circuit

Package Outline Dimensions



| DIM | Inches | | Millimeters | | DIM | Inches | | Millimeters | |
|-----|--------|-------|-------------|-------|------------------|-----------|-------|-------------|-------|
| | Min | Max | Min | Max | | Min | Max | Min | Max |
| A | 0.086 | 0.094 | 2.18 | 2.39 | e | 0.090 BSC | | 2.29 BSC | |
| A1 | - | 0.005 | - | 0.127 | H | 0.370 | 0.410 | 9.40 | 10.41 |
| b | 0.020 | 0.035 | 0.508 | 0.89 | L | 0.055 | 0.070 | 1.40 | 1.78 |
| b2 | 0.030 | 0.045 | 0.762 | 1.14 | L1 | 0.108 REF | | 2.74 REF | |
| b3 | 0.205 | 0.215 | 5.21 | 5.46 | L2 | 0.020 BSC | | 0.508 BSC | |
| c | 0.018 | 0.024 | 0.457 | 0.61 | L3 | 0.035 | 0.065 | 0.89 | 1.65 |
| c2 | 0.018 | 0.023 | 0.457 | 0.584 | L4 | 0.025 | 0.040 | 0.635 | 1.016 |
| D | 0.213 | 0.245 | 5.41 | 6.22 | L5 | 0.045 | 0.060 | 1.14 | 1.52 |
| D1 | 0.205 | - | 5.21 | - | θ_1° | 0° | 10° | 0° | 10° |
| E | 0.250 | 0.265 | 6.35 | 6.73 | θ° | 0° | 15° | 0° | 15° |
| E1 | 0.170 | - | 4.32 | - | - | - | - | - | - |

Suggested Pad Layout



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